What is claimed is:

1. A semiconductor light emitting element that is made by using the lateral growth function of semiconductor crystal while providing an ELO mask on a crystal growth surface of a crystal growth substrate, wherein at least part of a sidewall of the ELO mask is provided with an inclined plane that is inclined to the crystal growth surface such that the semiconductor crystal to be formed on the ELO mask substantially has no void.

2. The semiconductor light emitting element according to claim 1, wherein:

at least part of the inclined plane is curved.

3. The semiconductor light emitting element according to claim 2, wherein:

the shape of ELO mask in cross section vertical to the crystal growth surface is formed nearly semicircular, nearly semi-elliptic or partially either of these shapes.

4. The semiconductor light emitting element according to claim 1, wherein:

the shape of ELO mask in cross section vertical to the crystal growth surface is formed nearly isosceles triangular or nearly isosceles trapezoidal with flat top.

5. The semiconductor light emitting element according to claim 1, wherein:

the shape of ELO mask on the crystal growth surface is formed like a spot or a nearly stripe.

6. The semiconductor light emitting element according to claim 1, wherein:

the crystal growth substrate is of sapphire.

7. The semiconductor light emitting element according to claim 1, wherein:

the semiconductor crystal is of $Al_xGa_{1-x}N$ $(0 \leqq x \leqq 1)$.

8. The semiconductor light emitting element according to claim 1, wherein:

the semiconductor light emitting element is a flip-chip type LED, the refractive index of the ELO mask is set to be greater than that of the crystal growth substrate and smaller than that of the semiconductor crystal.

9. A method of making a semiconductor light emitting element, comprising the steps of:

forming an ELO mask on a crystal growth surface of a crystal growth substrate;

providing at least part of a sidewall of the ELO mask with an inclined plane that is inclined to the crystal growth surface; and

growing semiconductor crystal on the crystal growth surface of the crystal growth substrate.

10. The method according to claim 9, wherein:

at least part of the inclined plane is curved.

11. The method according to claim 10, wherein:
the shape of ELO mask in cross section vertical to the crystal growth surface is formed nearly semicircular, nearly semi-elliptic or partially either of these shapes.

12. The method according to claim 9, wherein:
the shape of ELO mask in cross section vertical to the crystal growth surface is formed nearly isosceles triangular or nearly isosceles trapezoidal with flat top.

13. The method according to claim 9, wherein:
the shape of ELO mask on the crystal growth surface is formed like a spot or a nearly stripe.

14. The method according to claim 9, wherein:
the crystal growth substrate is of sapphire.

15. The method according to claim 9, wherein:
the semiconductor crystal is of $Al_xGa_{1-x}N$ ($0 \leqq x \leqq 1$).

16. The method according to claim 15, wherein:
the amount of trimethylgallium ($Ga(CH_3)_3$) to be supplied per unit time in growing the semiconductor crystal is 100 μ mol/min. or more and 800 μmol/min. or less.